Date	User	Material	Recipe	Substrate temperature	Measured Thickness	Dep.time	Dep.time	JAW EC-400 (Woolam Spectroscopic Ellipsometer)		Dep.rate	Stress	HF etch rate wafer	HF etch rate pieces	LPD (light point defects)		AVG dep.rate	AVG+10%	AVG-10%	AVG index@632.8	AVG+2%	AVG-2%	Additional Notes	Brian Ling, PM
1/1/2012	User	SiN	SiN_10	250 °C	(Å)	min/ sec	sec	index @ 632.8nm	index@1550nm	(nm/min)	Tensile(+456MPa)	(nm/min)	(nm/min)	before dep.	after dep.								
																							12/9/2013 Pattern-Steven W.
01/06/14	**Biljana**	**SiN**	**SiN_10**	250	**1055.25**	9'28.1"	568.1	**1.949**	1.899	**11.15**	**571.87**			78	547	**11.26**	**12.39**	**10.14**	**1.959**	**1.998**	**1.920**	4" Si wafer	
01/23/14	**Biljana**	**SiN**	**SiN_10**	250	**1133.40**	9'28.1"	568.1	**1.935**	1.890	**11.97**	**446.88**	**90.66**		137	377	**11.26**	**12.39**	**10.14**	**1.959**	**1.998**	**1.920**	4" Si wafer	1/23/14
02/03/14	**Biljana**	**SiN**	**SiN_10**	250	**1046.60**	9'28.1"	568.1	**1.937**	1.893	**11.05**	**486.75**	**81.21**		322	604	**11.26**	**12.39**	**10.14**	**1.959**	**1.998**	**1.920**	4" Si wafer	
02/19/14	**Biljana**	**SiN**	**SiN_10**	250	**1030.66**	9'28.1"	568.1	**1.935**	1.890	**10.89**	**353.92**	**77.32**		75	323	**11.26**	**12.39**	**10.14**	**1.959**	**1.998**	**1.920**	4" Si wafer, some grouped particles	2/14/14 Silane change

Commment: Run SiN deposition1000A every two weeks, on Fridays! Measure thickness, index, dep.rate(center of the wafer) and HF etch rate(wafer, three points)
Run SiN deposition1000A every 4 weeks, on Fridays! Measure LPD, stress, thickness uniformity

Avg index@632.8	**1.939**	**Avg Dep.Rate**	**11.26**
Avg+2%	**1.978**	**Avg +10%**	**12.39**
Avg-2%	**1.901**	**Avg - 10%**	**10.14**

*** Ning, 2000A, stress=260MPa**
*** Ning, 2000A, HF e.r.=36nm/min**

***Bilja, 1000A, stress~+350MPa**
****Bilja, 3000A, HF e.r.~52nm/min**

SIN uniform HF etch!